ABSTRACT OF THE DISCLOSURE

In order to eliminate the difference in ESD resistance caused by polarities of excessive voltages applied to an external terminal and enhance ESD resistance of a semiconductor integrated circuit device to both the positive and negative overvoltages, a protection element having a thyristor structure, for protecting an internal circuit from the positive overvoltage and a protection element made up of a diode D1 for protecting the internal circuit from the negative overvoltage are provided between the external terminal and a ground potential.